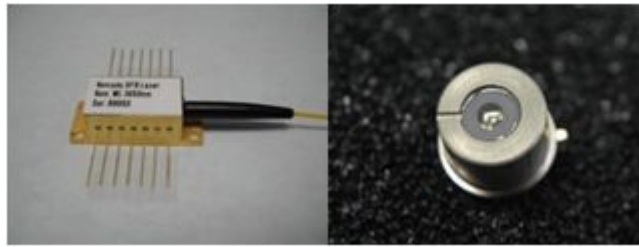


DFB-0795-100-T03, DFB Diode Laser

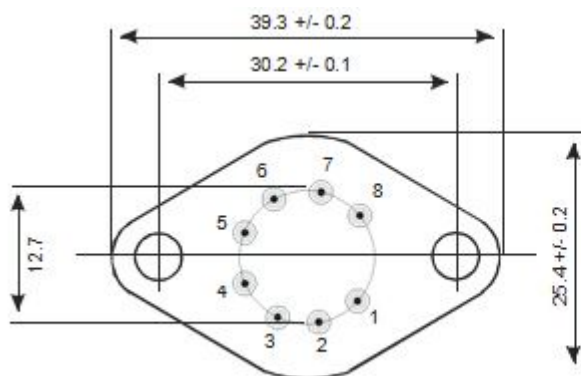


Wavelength: Selection for Rubidium D1 line available
 The DFB-0795-080-T03 is a high power MOVPE grown GaAsP/AlGaAs Distributed Feedback diode laser. The chips are mounted in TO3 can with Peltier cooler. Fully mode-hop free tuning selection available upon request

Specification(The characteristics are measured at 25°C operation temperature.)

Parameter	Symbol	Unit	min.	typ.	max.
Center Wavelength	λ_c	nm	794	795	796
Spectral Width	$\Delta\lambda$	MHz		3	10
Temperature Coefficient	$\Delta\lambda/\Delta T$	nm/K		0.06	
Laser Current Coefficient	$\Delta\lambda/\Delta I$	nm/mA		0.003	
Output Power	P_{opt}	mW	10		80
Slope Efficiency	η	mW/mA	0.6	0.8	1.0
Threshold Current	I_{th}	mA			70
Operation Current @ $P_{opt} = 80\text{mW}$	I_{opt}	mA			190
Beam Divergence \parallel (FWHM)	θ_{\parallel}	deg.	6	8	10
Beam Divergence \perp (FWHM)	θ_{\perp}	deg.	18	21	24
Polarization				TM	
Mode Structure			fundamental transverse mode		

Laser Mount: T03 - can with Peltier cooler



- Pin 1: TEC (+)
- Pin 2: NTC Thermistor 10k Ω at 25°C
- Pin 3: NTC Thermistor 10k Ω at 25°C
- Pin 4: Laser Cathode (-)
- Pin 5: Laser Anode (+)
- Pin 6: Photodiode Anode (+)
- Pin 7: Photodiode Cathode (-)
- Pin 8: TEC (-)